

入射光

半導体受光素子

## **Patent Abstracts of Japan**

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TITLE

**SOLID-STATE PHOTOSENSOR** 

ABSTRACT :

PURPOSE: To prevent output from being saturated in spite of incidence of strong light by using glass whose transmission factor changes according to the strength of the incident light for a case front corresponding to a light-receiving surface.

CONSTITUTION: A semiconductor photosensor chip 1 is mounted on a ceramic case 2 and wired by an Al wire 3. For instance, what is called photochromic glass that is the mixture of alkali-alumino-borosilicate glass and silver chloride is used for a glass cap 4 of the case front to become the light-receiving surface. In this way, the photochromic glass is blackened when exposed to strong light so that light incident inside a solid-state photosensor is reduced. Accordingly, when the photosensor is used for a camera or the like, the fixed picture quality can be obtained even when exposed to strong light without attaching a complex function such as an automatic iris to a camera.

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